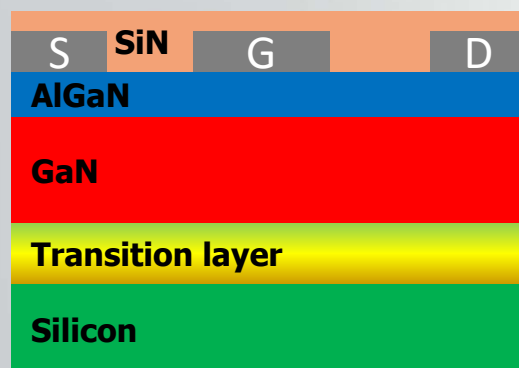


# Projet HEMT 2

Début 02/11/2015 – 18 mois

Audrey Chapelle



Ref 1

6 niveaux de masque  
35 étapes

$\text{Si}_3\text{N}_4$  deposition 50nm LPCVD



$\text{Si}_3\text{N}_4$  deposition 50nm LPCVD

$\text{Si}_3\text{N}_4/\text{AlGaIn}/\text{GaIn}$  RIE etch



## $\text{Si}_3\text{N}_4$ (2) deposition



$\text{Si}_3\text{N}_4$  (2) deposition

$\text{Si}_3\text{N}_4$  etch 100nm



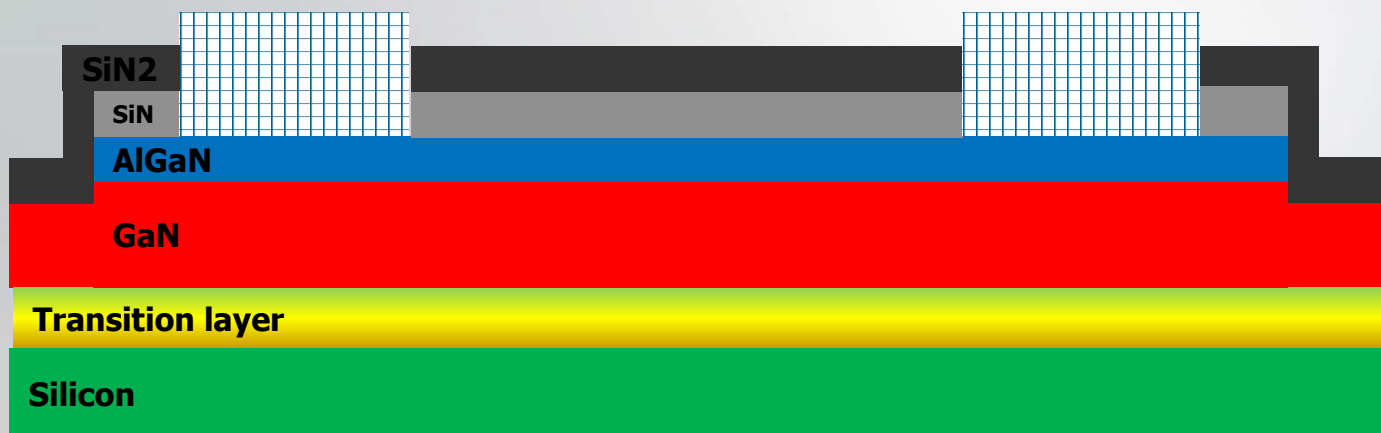
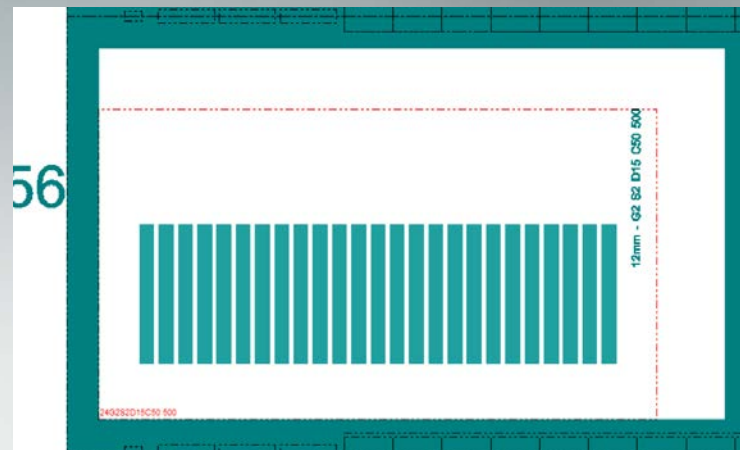
$\text{Si}_3\text{N}_4$  (2) deposition

$\text{Si}_3\text{N}_4$  etch 100nm

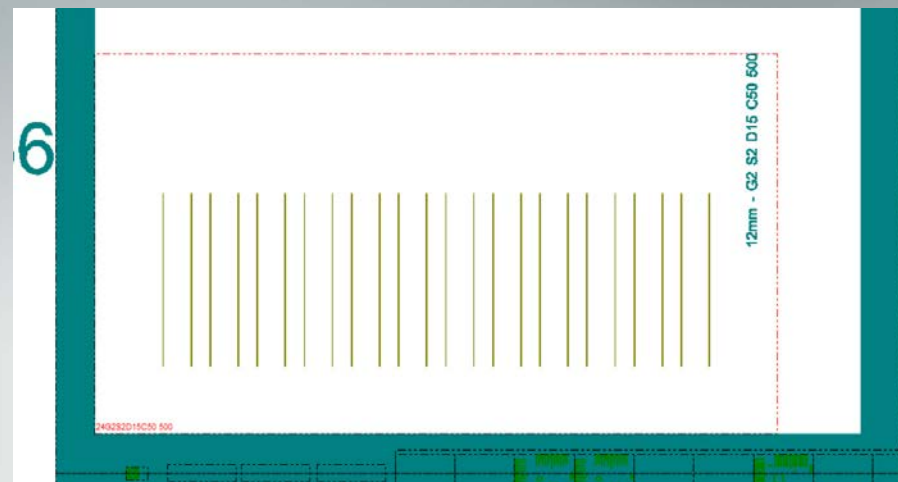
Ti/Al/Ni/Ti evap



Contact source&drain  
Ti/Al/Ni/Ti  
15/75/40/10nm



SiN etch (100nm)







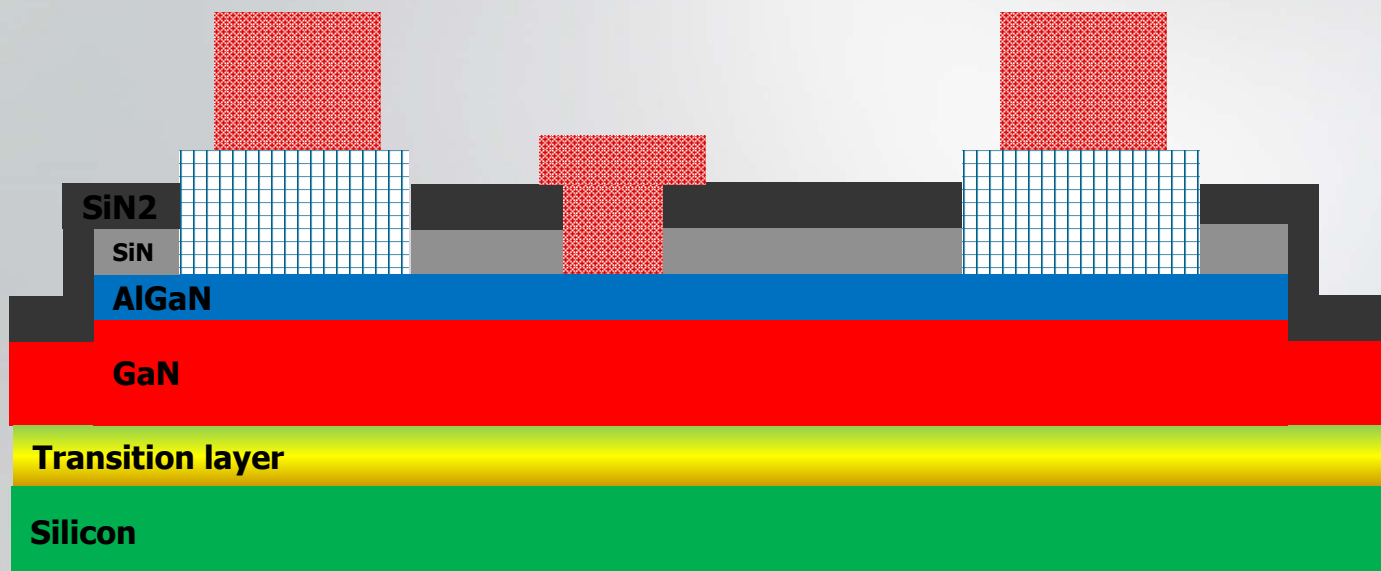
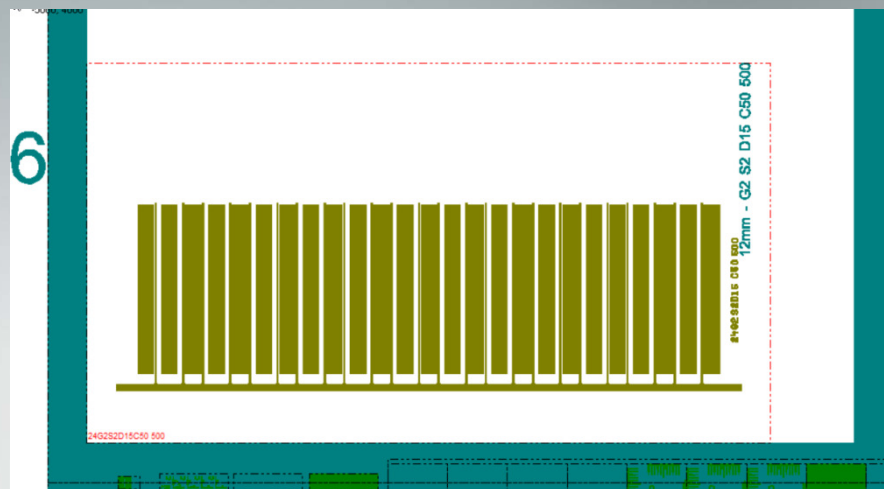
TOULOUSE  
TECH  
TRANSFER

Ni/Pt/Ti evap



Metal 1 G + S&D  
Ni/Pt/Ti  
80/20/20nm

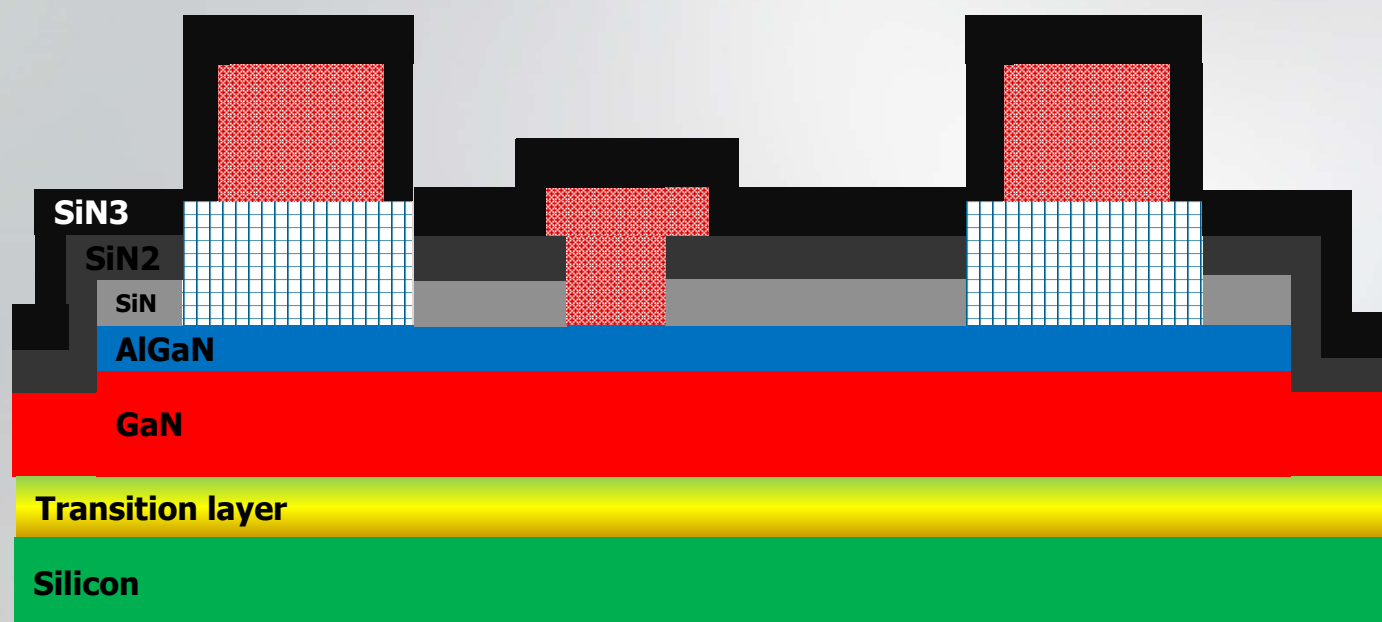
6



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SiN (3) deposition 100nm

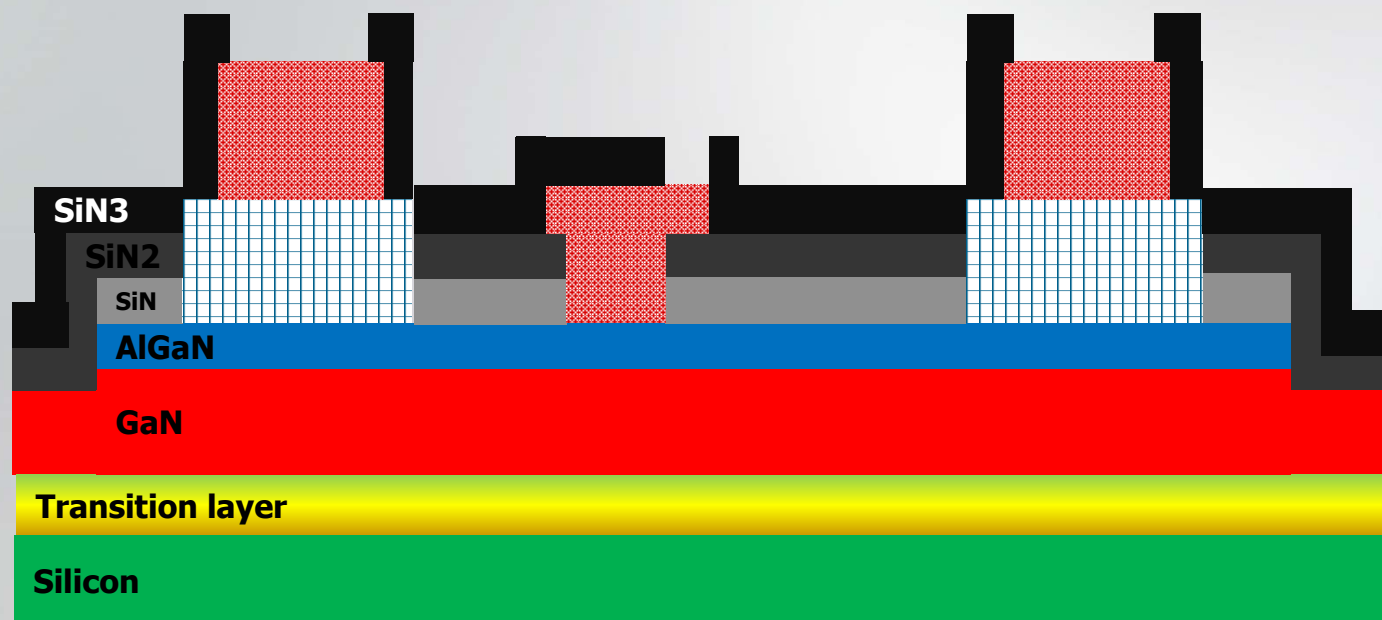
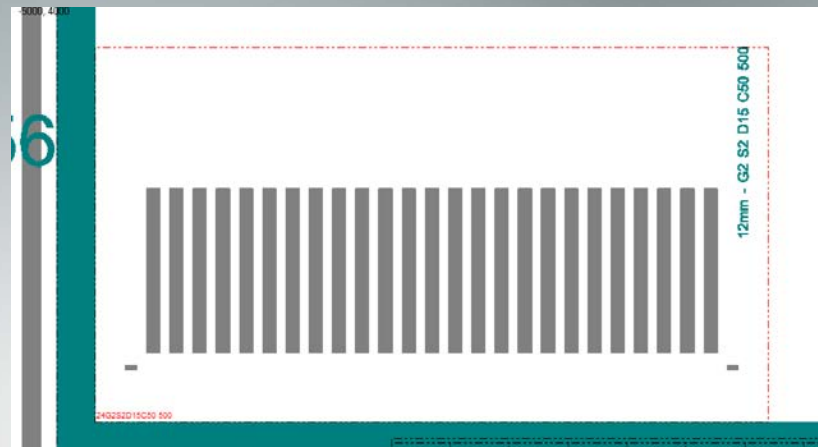




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SiN (3) deposition 100nm

SiN etch



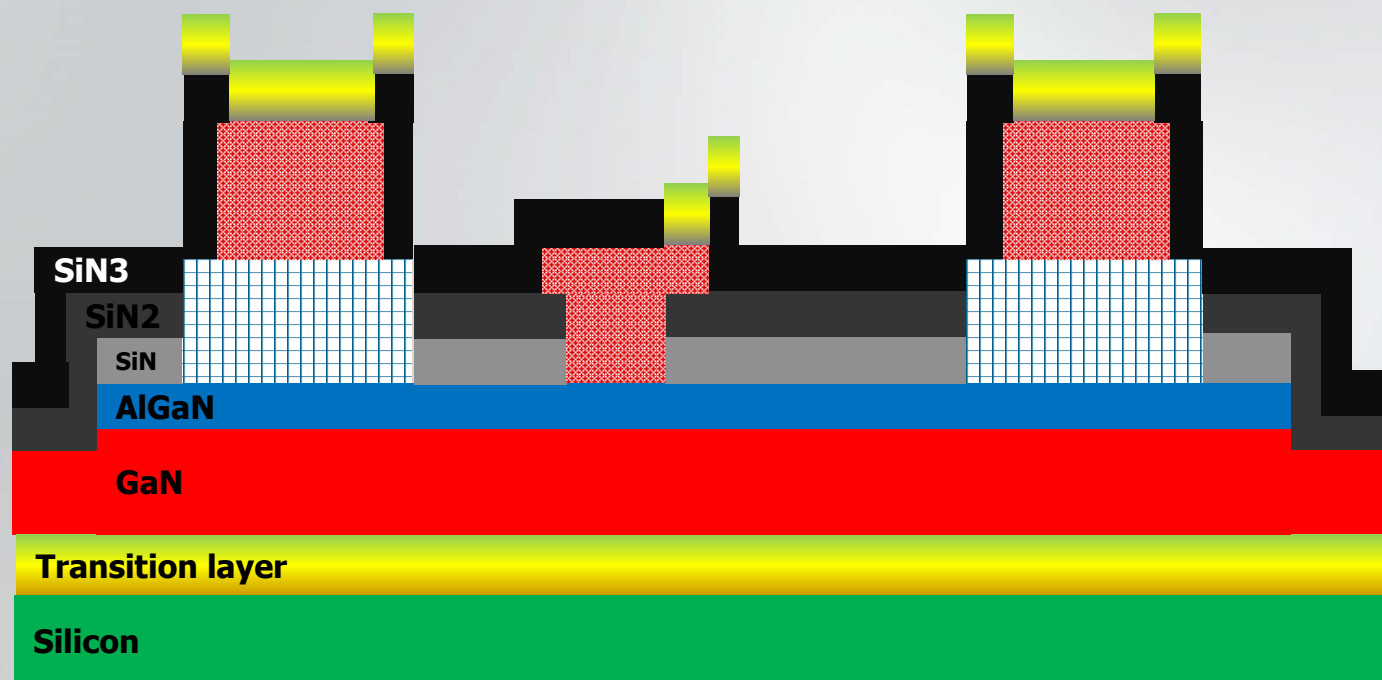
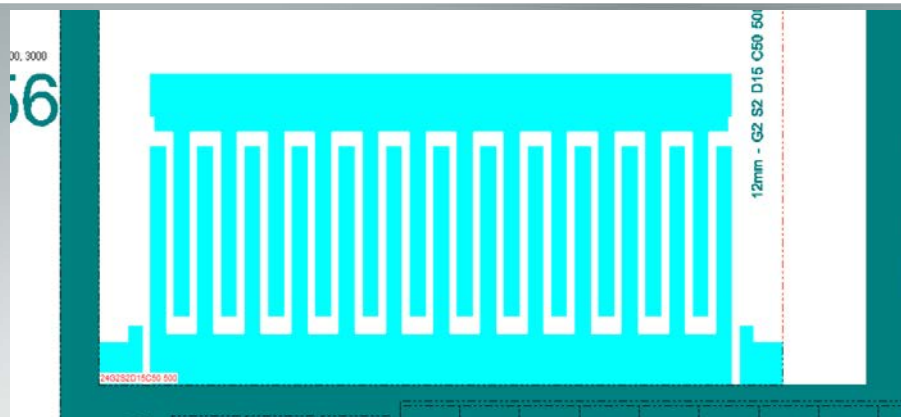
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TRANSFER

Ti/Au evap



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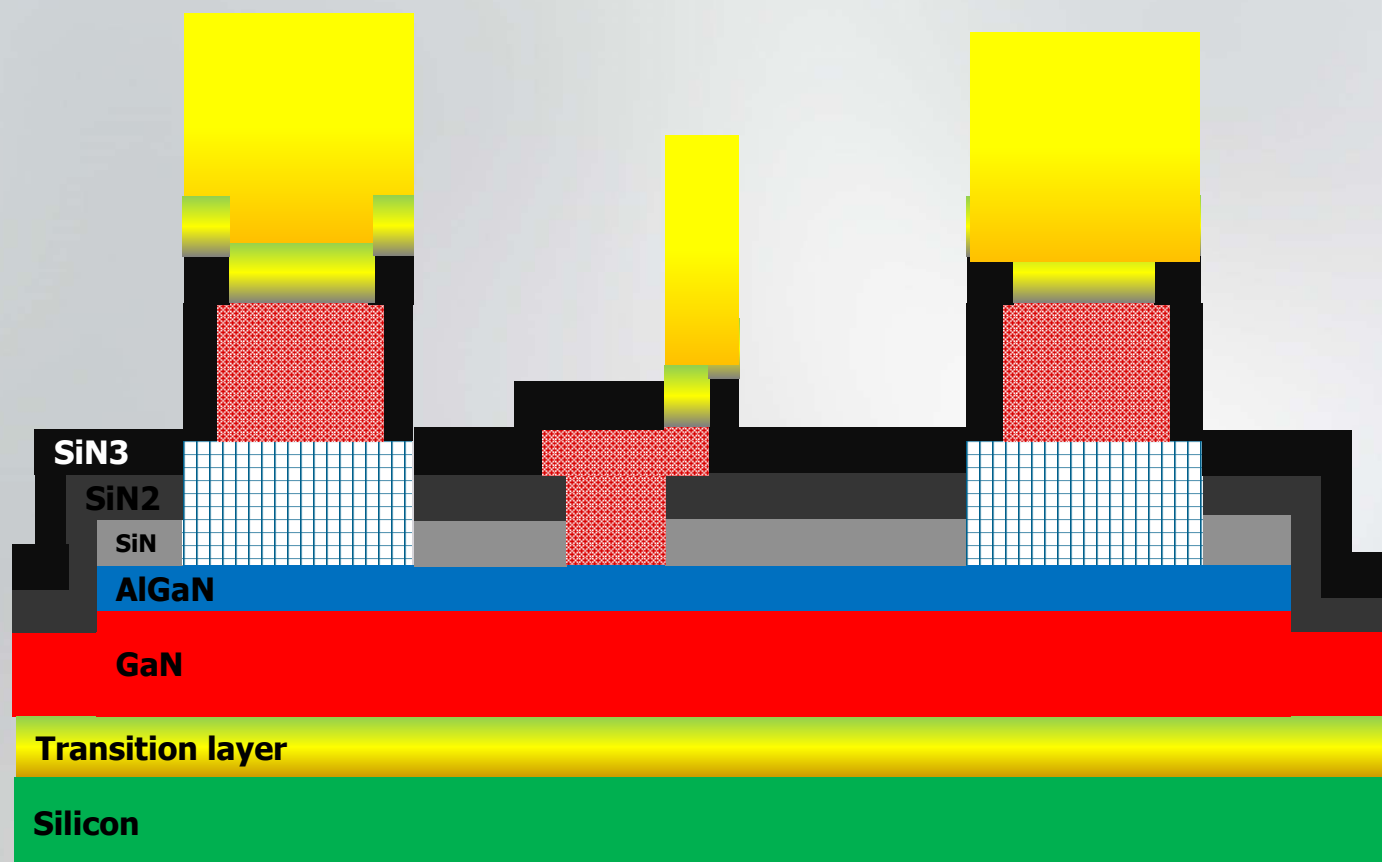
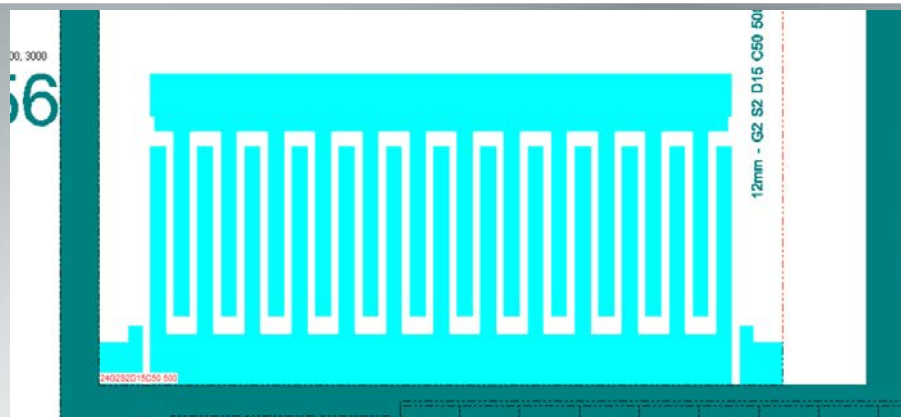
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TRANSFER

Ti/Au evap

Au electrodeposition 3,5 $\mu$ m



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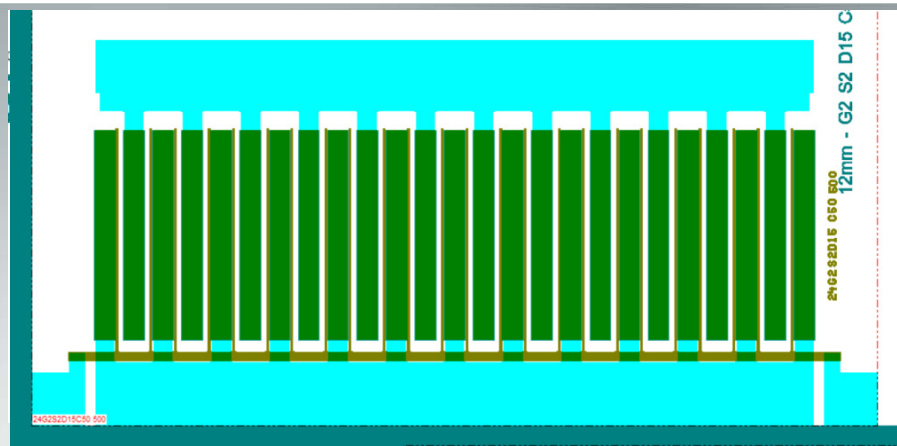
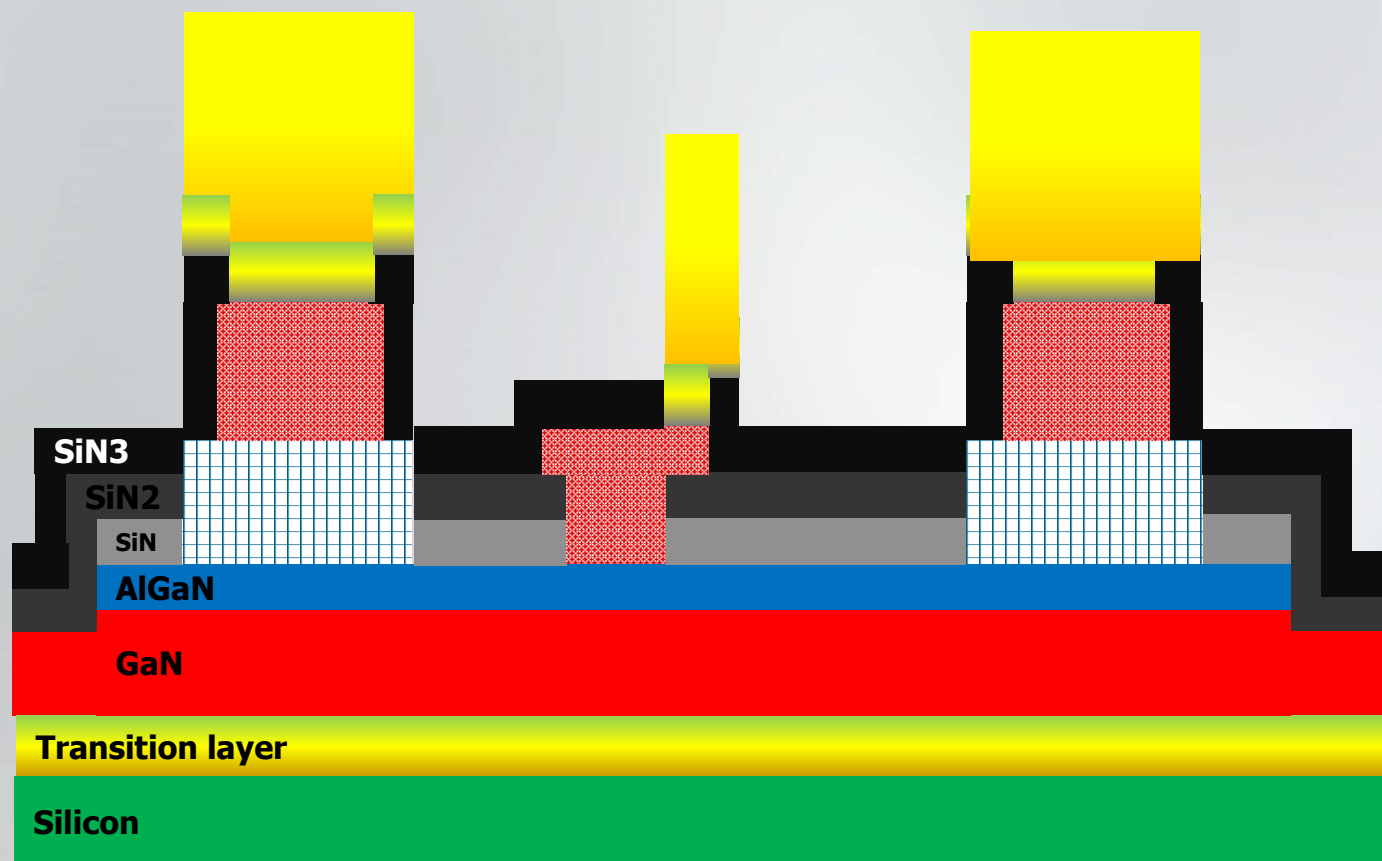
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TOULOUSE  
TECH  
TRANSFER

Ti/Au evap

Au electrodeposition 3,5 $\mu$ m



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